

### **Optical Absorption in Silicon**

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# **Optical absorption in silicon**

- Outline
  - Introduction
  - Our apparatus
  - Sample measurements
  - Discussion
  - Future directions



### Introduction

- Previous work in Glasgow
  - Photothermal Commonpath Interferometer
    - Initially used for bulk silicon absorption measurements
    - Issues with high irradiance causing multi-photon effects
    - Currently focussing on coating measurements on various substrates with this instrument
- All this work
  - Photothermal Deflection or "Mirage"
  - Mainly using position modulation<sup>1</sup>
    - Maximum signal when beams are aligned and not offset
    - Nominally more signal per watt than amplitude modulation (although that is often not the limitation)









# **Room Temperature Measurement of:**

- AEI samples
  - Some interesting surface effects
- Glasgow sample
- LMA sample
  - Cross reference calibration sample

resistivity
(5 kΩ.cm, & ~30k - 80 kΩ.cm)

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(>10 kΩ.cm)
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(?)



## **Vertical scans**

Absorption signal at a single position

•Normalise signal from lock-in amplifier to pump and probe power

•Use known absorption of calibration sample to get our calibration factor





### **Horizontal scan**

• Absorption along a line through the sample



Position along crystal



### AEI sample #1, horizontal & vertical scans (5 kΩ.cm)



AEI Sample 1, horizontal scan

#### Vertical scan near centre

Horizontal scan

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All subsequent horizontal scans shown were taken at ~ 7 mm horizontal resolution



### AEI sample #2, horizontal & vertical scans (30-80 kΩ.cm)



#### Horizontal scan

Vertical scan near centre



#### AEI sample #3, horizontal & vertical scans (30-80 kΩ.cm)



Horizontal scan

Vertical scan near centre



### Glasgow sample, horizontal & vertical scans (>10 kΩ.cm)



Horizontal scan

Vertical scan near centre

2-photon effects becoming significant – horizontal scan is taken with higher pump power and has contribution of several ppm/cm due to this



### LMA sample, horizontal & vertical scans



#### Horizontal scan

Vertical scan near centre

Sample previously measured at LMA as between 20 & 30 ppm/cm This measurement gives about 28 ppm/cm and if we remove ~2 ppm/cm due to non-linear effects -> 26 ppm/cm





pump irradiance  $(W/cm^2)$ 



## Discussion

- Some samples show surface absorption
- Understand the differences between samples and determine where surface absorption comes from (not intrinsic)
- Surface absorption
  - Use etching to help determine where absorption occurs
    - Oxide layer first
    - First few/several nanometers of silicon
    - Further polish or etch as required



## Discussion

- In our set-up we want to look at:
  - Signal size vs position better understanding
  - Geometric effects (e.g. change in beam size for longer samples)
    - Enable better measurement of absorption through the sample
  - Further increase beam size to reduce non-linearities
    - Currently see equivalent of a few ppm/cm extra absorption for ~5 watts pump
- Look at more detail at resistivity and absorption
  - Seems that resitivities of 1kΩ.cm and less correlate well with absorption but not higher values?



### **Future work**

- Cryogenic measurements
  - Cryostat just setup
  - Started looking at a highly doped sample
    - Alpha ~ 0.05 /cm
  - Indications are that our measurement confirms absorption does not decrease with temperature



## Conclusions

- Swapped samples for testing with LMA and agree on absorption values to within 20%
- Measured room temperature loss of sub-10 ppm/cm in "intrinsic" silicon (Hanover sample)
- Aiming to provide understanding of (non-intrinsic) surfaces losses in these samples
- Starting to look at cryogenic absorption

### Thank-you